IRFP17N50L, SiHFP17N50L

Vishay Siliconix



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R _{thJA}	-	62	
Case-to-Sink, Flat, Greased Surface	R _{thCS}	0.50	-	°C/W
Maximum Junction-to-Case (Drain)	R _{thJC}	-	0.56	

PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static			<u> </u>				
Drain-Source Breakdown Voltage	V _{DS}	V _{GS} :	= 0 V, I _D = 250 μA	500	-	-	V
V _{DS} Temperature Coefficient	$\Delta V_{DS}/T_{J}$	Reference	e to 25 °C, I _D = 1 mA ^d	-	0.60	-	V/°C
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	3.0	-	5.0	V
Gate-Source Leakage	I _{GSS}		$V_{GS} = \pm 30 \text{ V}$	-	-	± 100	nA
Zava Cata Valtaga Dvain Curvent	1	V _{DS} =	= 500 V, V _{GS} = 0 V	-	-	50	μΑ
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 400 \	/, V _{GS} = 0 V, T _J = 125 °C	-	-	2.0	mA
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	$I_D = 9.9 A^b$	-	0.28	0.32	Ω
Forward Transconductance	9 _{fs}	V _{DS} :	= 50 V, I _D = 9.9 A ^b	11	-	-	S
Dynamic							
Input Capacitance	C _{iss}		$V_{GS} = 0 V$,	_	2760	-	
Output Capacitance	Coss		$V_{DS} = 25 \text{ V},$	-	325	-	1
Reverse Transfer Capacitance	C _{rss}	f = 1	.0 MHz, see fig. 5	_	37	-]
Output Canaditanas	0		V _{DS} = 1.0 V , f = 1.0 MHz	-	3690	-	- pF -
Output Capacitance	C_{oss}		V _{DS} = 400 V , f = 1.0 MHz	-	84	-	
Effective Output Capacitance	Coss eff.	V _{GS} = 0 V	V _{DS} = 0 V to 400 V	-	159	-	
Effective Output Capacitance (Energy Related)	C _{oss} eff. (ER)			-	120	-	
Internal Gate Resistance	R _g	f = 1	MHz, open drain	-	1.4	-	Ω
Total Gate Charge	Qg		1 10 4 1/ 100 1/	-	-	130	
Gate-Source Charge	Q _{gs}	V _{GS} = 10 V		-	-	33	nC
Gate-Drain Charge	Q _{gd}			-	-	59	
Turn-On Delay Time	t _{d(on)}	.,	050 1/ 1 40 4	-	21	-	
Rise Time	t _r	$V_{DD} = 250 \text{ V, } I_D = 16 \text{ A}$ $R_G = 7.5 \Omega, V_{GS} = 10 \text{ V}$ see fig. 14a and 14bb		-	51	-	ns
Turn-Off Delay Time	t _{d(off)}			-	50	-	
Fall Time	t _f	366 1	ig. 14a and 14b	-	28	-	1
Drain-Source Body Diode Characteristic	es						
Continuous Source-Drain Diode Current	Is	MOSFET symi	bol	-	-	16	
Pulsed Diode Forward Current ^a	I _{SM}	integral reverse p - n junction diode		-	-	64	- A
Body Diode Voltage	V_{SD}	T _J = 25 °C	$C, I_S = 16 A, V_{GS} = 0 V^b$	-	-	1.5	V
Body Diode Reverse Recovery Time	t _{rr}	T _J = 25 °C	J = 25 °C		170	250	ns
		T _J = 125 °C	I _F = 16 A,	-	220	330	113
Rody Diode Reverse Possyon, Charge	Q _{rr}	T _J = 25 °C	dl/dt = 100 A/µs ^b	_	470	710	μC
Body Diode Reverse Recovery Charge		T _J = 125 °C		-	810	1210	μΟ
Reverse Recovery Current	I _{RRM}		T _J = 25 °C	-	7.3	11	
Forward Turn-On Time	t _{on}	Intrinsic tu	rn-on time is negligible (turn-	on is dor	ninated b	v I e and	I ^D)

Notes

<sup>a. Repetitive rating; pulse width limited by maximum junction temperature (see fig. 11).
b. Pulse width ≤ 300 µs; duty cycle ≤ 2 %.
c. C_{OSS} eff. is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising fom 0 % to 80 % V_{DS}. C_{OSS} eff. (ER) is a fixed capacitance that stores the same energy as C_{OSS} while V_{DS} is rising fom 0 % to 80 % V_{DS}.</sup>



TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

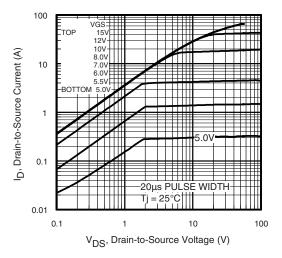


Fig. 1 - Typical Output Characteristics

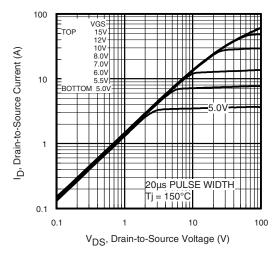


Fig. 2 - Typical Output Characteristics

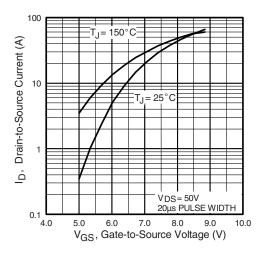


Fig. 3 - Typical Transfer Characteristics

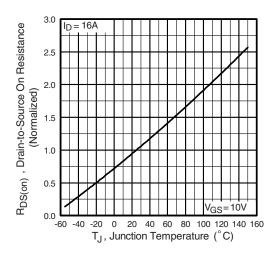


Fig. 4 - Normalized On-Resistance vs. Temperature



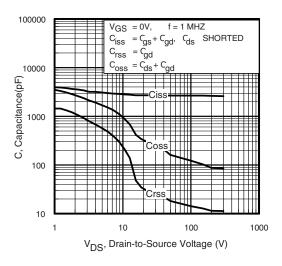


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

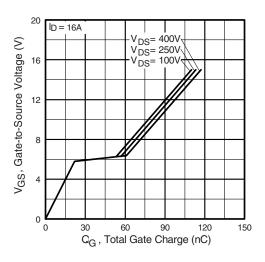


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

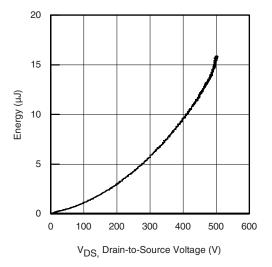


Fig. 6 - Typ. Output Capacitance Stored Energy vs. V_{DS}

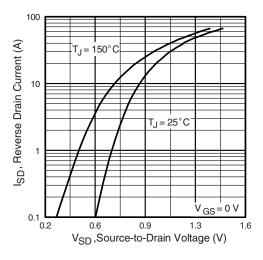


Fig. 8 - Typical Source-Drain Diode Forward Voltage



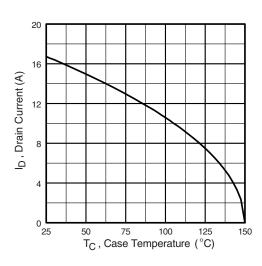


Fig. 9 - Maximum Drain Current vs. Case Temperature

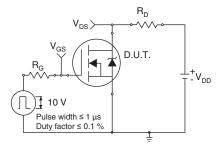


Fig. 10a - Switching Time Test Circuit

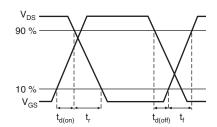


Fig. 10b - Switching Time Waveforms

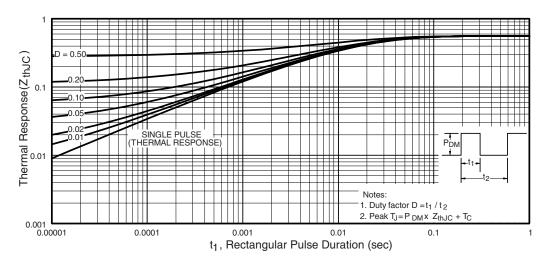


Fig. 11 - Maximum Effective Transient Thermal Impedance, Junction-to-Case



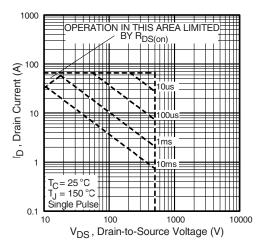


Fig. 12 - Maximum Safe Operating Area

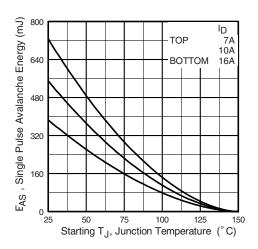


Fig. 13 - Maximum Avalanche Energy vs. Drain Current

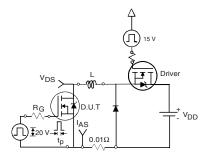


Fig. 14a - Unclamped Inductive Test Circuit

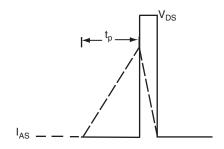


Fig. 14b - Unclamped Inductive Waveforms

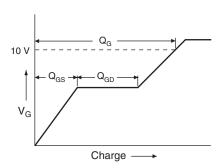


Fig. 15a - Basic Gate Charge Waveform

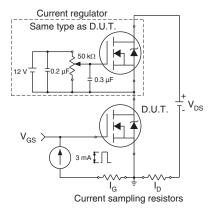
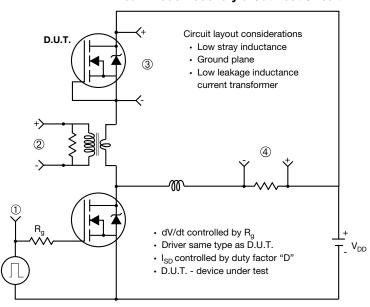


Fig. 15b - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



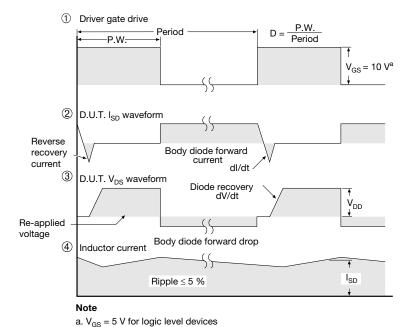


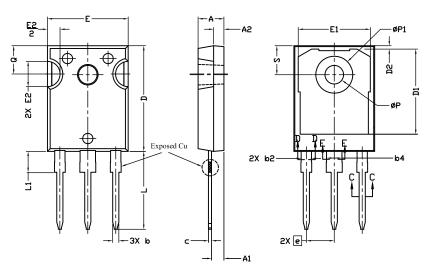
Fig. 16. For N-Channel

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?91205.

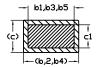


TO-247AC (High Voltage)

VERSION 1: FACILITY CODE = 9







Section C--C,D--D,E--E

	MILLIN		
DIM.	MIN.	MAX.	NOTES
Α	4.83	5.21	
A1	2.29	2.55	
A2	1.50	2.49	
b	1.12	1.33	
b1	1.12	1.28	
b2	1.91	2.39	6
b3	1.91	2.34	
b4	2.87	3.22	6, 8
b5	2.87	3.18	
С	0.55	0.69	6
c1	0.55	0.65	
D	20.40	20.70	4

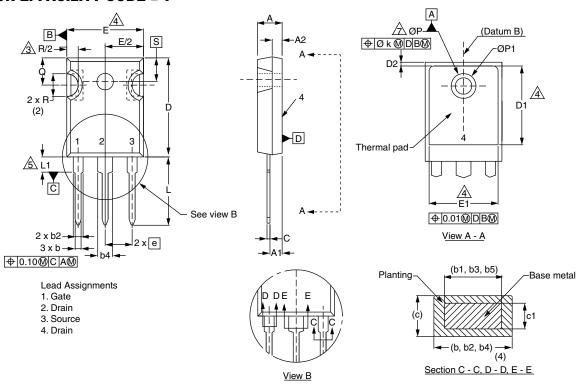
	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
D1	16.25	16.85	5
D2	0.56	0.76	
E	15.50	15.87	4
E1	13.46	14.16	5
E2	4.52	5.49	3
е	5.44 BSC		
L	14.90	15.40	
L1	3.96	4.16	6
ØΡ	3.56	3.65	7
Ø P1	7.19 ref.		
Q	5.31	5.69	
S	5.54	5.74	

Notes

- (1) Package reference: JEDEC® TO247, variation AC
- (2) All dimensions are in mm
- (3) Slot required, notch may be rounded
- (4) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm per side. These dimensions are measured at the outermost extremes of the plastic body
- (5) Thermal pad contour optional with dimensions D1 and E1
- (6) Lead finish uncontrolled in L1
- $^{(7)}$ Ø P to have a maximum draft angle of 1.5 $^\circ$ to the top of the part with a maximum hole diameter of 3.91 mm
- (8) Dimension b2 and b4 does not include dambar protrusion. Allowable dambar protrusion shall be 0.1 mm total in excess of b2 and b4 dimension at maximum material condition

Revision: 19-Oct-2020 1 Document Number: 91360

VERSION 2: FACILITY CODE = Y



	MILLIMETERS		
DIM.	MIN.	MAX.	NOTES
Α	4.58	5.31	
A1	2.21	2.59	
A2	1.17	2.49	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.53	2.39	
b3	1.65	2.37	
b4	2.42	3.43	
b5	2.59	3.38	
С	0.38	0.86	
c1	0.38	0.76	
D	19.71	20.82	
D1	13.08	-	

	MILLIN		
DIM.	MIN.	MAX.	NOTES
D2	0.51	1.30	
E	15.29	15.87	
E1	13.72	-	
е	5.46	5.46 BSC	
Øk	0.254		
L	14.20	16.25	
L1	3.71	4.29	
ØΡ	3.51	3.66	
Ø P1	-	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

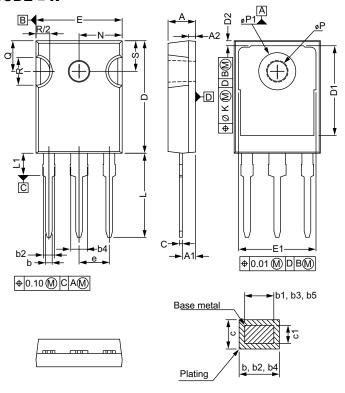
Notes

- (1) Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")
- (7) Outline conforms to JEDEC outline TO-247 with exception of dimension c

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VERSION 3: FACILITY CODE = N



	MILLIMETERS		
DIM.	MIN.	MAX.	
Α	4.65	5.31	
A1	2.21	2.59	
A2	1.17	1.37	
b	0.99	1.40	
b1	0.99	1.35	
b2	1.65	2.39	
b3	1.65	2.34	
b4	2.59	3.43	
b5	2.59	3.38	
С	0.38	0.89	
c1	0.38	0.84	
D	19.71	20.70	
D1	13.08	-	

	MILLIMETERS		
DIM.	MIN.	MAX.	
D2	0.51	1.35	
E	15.29	15.87	
E1	13.46	-	
е	5.46 BSC		
k	0.254		
L	14.20	16.10	
L1	3.71	4.29	
N	7.62 BSC		
Р	3.56	3.66	
P1	=	7.39	
Q	5.31	5.69	
R	4.52	5.49	
S	5.51 BSC		

ECN: E20-0545-Rev. F, 19-Oct-2020

DWG: 5971

Notes

- ⁽¹⁾ Dimensioning and tolerancing per ASME Y14.5M-1994
- (2) Contour of slot optional
- (3) Dimension D and E do not include mold flash. Mold flash shall not exceed 0.127 mm (0.005") per side. These dimensions are measured at the outermost extremes of the plastic body
- (4) Thermal pad contour optional with dimensions D1 and E1
- (5) Lead finish uncontrolled in L1
- (6) Ø P to have a maximum draft angle of 1.5 to the top of the part with a maximum hole diameter of 3.91 mm (0.154")

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